

T12T

Snubberless™, logic level and standard 12 A Triacs

Features

- Medium current Triac
- High static and dynamic commutation
- Low thermal resistance with clip bonding
- Packages is RoHS (2002/95/EC) compliant
- 600 V V_{RM}

Applications

- Value sensitive application
- General purpose ac line load switching
- Motor control circuits in power tools
- Small home appliances, lighting
- Inrush current limiting circuits
- Overvoltage crowbar protection

Description

Available in through-hole, the T12T series of Triacs can be used as on/off or phase angle control function in general purpose ac switching where high commutation capability is required.

This series can be designed-in in many value sensitive appliances thanks to the parameters guidance provided in the following pages.

Provides insulation rated at 2500 V rms (TO-220AB insulated package).

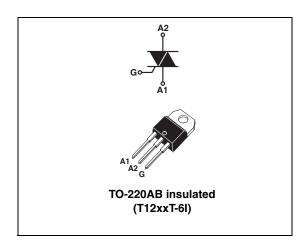


Table 1. Device summary

Order code	Symbol	Value
T1220T-6I T1235T-6I	I _{GT} 3Q Snubberless	20 / 35 mA
T1225T-6I	I _{GT} 4Q standard	25 mA
T1210T-6I	I _{GT} 3Q logic level	10 mA

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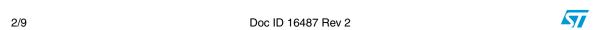
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Table 2. Absolute maximum ratings (limiting values; $T_i = 25$ °C, unless otherwise specified)

Symbol	Parameter	Value	Unit			
I _{T(RMS)}	On-state rms current (full sine wave)		T _c = 88 °C	12	Α	
1 -	Non repetitive surge peak on-state current (full	F = 50 Hz	t _p = 20 ms	90	Α	
I _{TSM}	cycle, T _j initial = 25 °C)	F = 60 Hz	$t_p = 16.7 \text{ ms}$	95	A	
l ² t	I ² t Value for fusing	t _p = 10 ms		54	A ² s	
dI/dt	Critical rate of rise of on-state current I_G = 2 x I_{GT} F = 60 Hz T_j = 125 °C		50	A/µs		
V _{DSM} / V _{RSM}	Non repetitive surge peak off-state voltage	t _p = 10 ms	T _j = 25 °C	V _{DRM} /V _{RRM} + 100	V	
I _{GM}	Peak gate current $t_p = 20 \mu s$ $T_j = 125 ^{\circ}C$		4	Α		
P _{G(AV)}	Average gate power dissipation $T_j = 125 ^{\circ}\text{C}$			1	W	
T _{stg}	Storage junction temperature range			- 40 to + 150	°C	
T _j	Operating junction temperature range			- 40 to + 125	°C	



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Table 3. Electrical characteristics ($T_j = 25$ °C, unless otherwise specified)

Cumbal	Test conditions	Quadrant		T12xxT			l lesia	
Symbol	Test conditions	Quadrant		T1210T	T1220T	T1225T	T1235T	Unit
I _{GT} ⁽¹⁾	$V_D = 12 \text{ V} R_L = 30 \Omega$	1 - 11 - 111	MAX.	10	20	25	35	mA
'GT \''		IV				40		
V _{GT}	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega,$ $T_j = 25 ^{\circ}\text{C}$ ALL		MAX.	1.3				V
V _{GD}	$V_D = V_{DRM}$, $R_L = 3.3 \text{ k}\Omega$, $T_j = 125 ^{\circ}\text{C}$	ALL	MIN.	0.2		V		
I _H (2)	I _T = 500 mA		MAX.	10	15	20	30	mA
	l _G = 1.2 l _{GT}	I - III	MAX.	20	35	40	50	mA
ΙL		IV				40		
		II		30	40	60	80	
dV/dt (2)	V _D = 67% V _{DRM,} gate open	T _j = 125 °C	MIN.	100	1000	100	2000	V/µs
u v/ui · /		$T_j = 150 {}^{\circ}C^{(3)}$		50	500	50	1000	
	(dV/dt)c = 0.1 V/μs			7		7		
	(dV/dt)c = 10 V/µs	T _j = 125 °C		3		3		
(di/dt)c (2)	Without snubber		MIN.		6		12	A/ms
(0)/01/0	$(dV/dt)c = 0.1 V/\mu s$		IVIIIN.	3		3		AVIIIS
	(dV/dt)c = 10 V/µs	$T_j = 150 {}^{\circ}C^{(3)}$		1		1		
	Without snubber				3		10	

^{1.} minimum $I_{\mbox{\scriptsize GT}}$ is guaranted at 5% of $I_{\mbox{\scriptsize GT}}$ max.

Table 4. Static characteristics

Symbol	Test conditions	Value	Unit		
V _T ⁽¹⁾	$I_{TM} = 17 \text{ A}, t_p = 380 \mu\text{s}$	T _j = 25 °C	MAX.	1.55	V
V _{TO} (1)	Threshold voltage	T _j = 125 °C	MAX.	0.85	V
R _D ⁽¹⁾	Dynamic resistance	T _j = 125 °C	MAX.	35	mΩ
I _{DRM}	$V_{DRM} = V_{RRM}$	T _j = 25 °C	MAX.	5	μΑ
		T _j = 125 °C	IVIAA.	1	mA
IRRM	$V_D = 0.9 \times V_{DRM}$	$T_j = 150 {}^{\circ}C^{(2)}$	TYP.	1.9	

^{1.} for both polarities of A2 referenced to A1.

^{2.} for both polarities of A2 referenced to A1.

^{3.} derating information for excess temperature above $T_j \, \text{max}$.

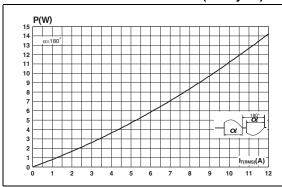
^{2.} derating information for excess temperature above $T_j \, \text{max}$.

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Table 5. Thermal resistance

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case (AC)	2.6	°C/W
R _{th(j-a)}	Junction to ambient (DC)	60	°C/W

Figure 1. Maximum power dissipation versus Figure 2. On-state rms current versus case rms on-state current (full cycle) temperature (full cycle)



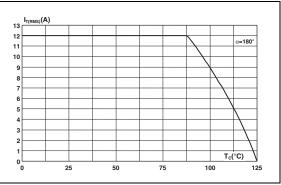


Figure 3. On-state rms current versus ambient temperature

2.0
1.5
1.0
0.5
0.0
2.5
50
75
100
125

Figure 4. Relative variation of thermal impedance versus pulse duration

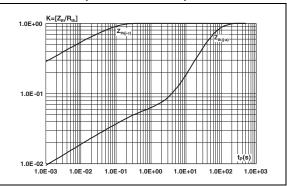
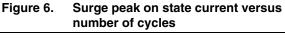
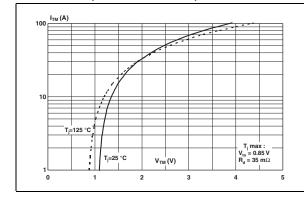
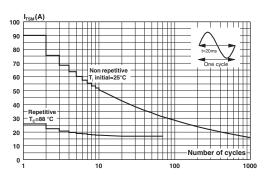


Figure 5. On state characteristics (maximum values)



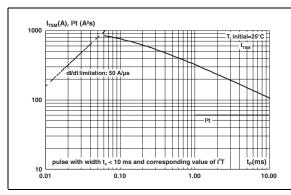




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Figure 7. Non repetitive surge peak on state Figure 8. Relative variation of gate trigger current for a sinusoidal current and gate trigger voltage versus junction temperature



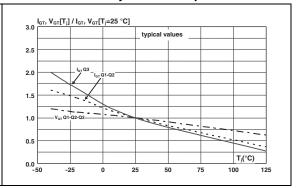
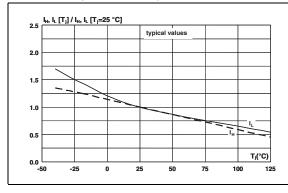
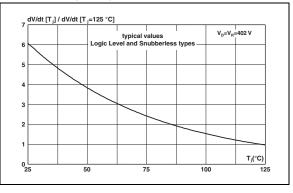


Figure 9. Relative variation of holding current and latching current versus junction temperature

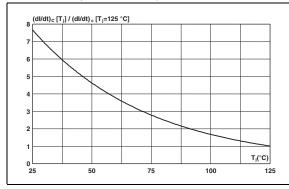
Figure 10. Relative variation of critical rate of decrease of main current versus (dV/dt)c

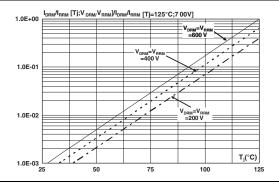




decrease of main current versus junction temperature

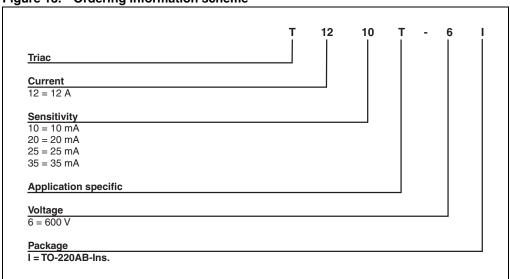
Figure 11. Relative variation of critical rate of Figure 12. Leakage current versus junction temperature for different values of blocking voltage (typical values)





2 Ordering information scheme

Figure 13. Ordering information scheme

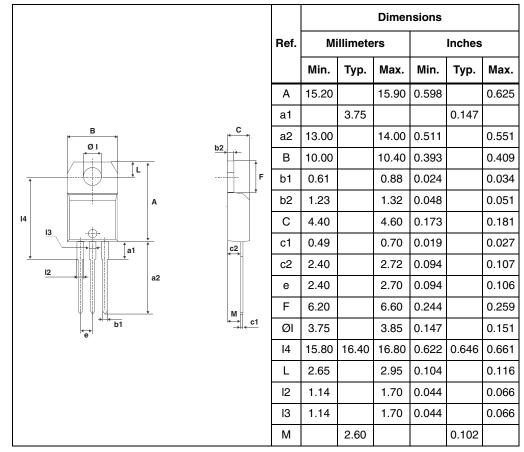


3 Package mechanical data

- Epoxy meets UL94, V0
- Lead-free packages

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 6. TO-220AB insulated dimensions





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Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
T1210T-6I	T1210T-6I				
T1220T-6I	T1220T-6I	TO-220AB-ins.	2.3 g	50	Tube
T1225T-6I	T1225T-6I	10-220AB-IIIS.	2.3 g	50	Tube
T1235T-6I	T1235T-6I				

5 Revision history

Table 8. Document revision history

Date	Revision	Changes
03-Dec-2009	1	Initial release.
18-Jan-2010	2	Updated pag.1.

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